# **Driver Transistors**

# **NPN Silicon**

#### **Features**

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBTA05LT1 MMBTA06LT1, SMMBTA06LT1	V <sub>CEO</sub>	60 80	Vdc
Collector - Base Voltage  MMBTA05LT1  MMBTA06LT1, SMMBTA06LT1	V <sub>CBO</sub>	60 80	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	500	mAdc
Electrostatic Discharge	ESD	HBM Class 3B MM Class C CDM Class IV	

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^{\circ}C$	P <sub>D</sub>	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C	P <sub>D</sub>	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

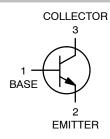
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in. 99.5% alumina.



### ON Semiconductor®

http://onsemi.com





SOT-23 CASE 318 STYLE 6

#### **MARKING DIAGRAMS**





MMBTA05LT1

MMBTA06LT1, SMMBTA06L

1H, 1GM = Specific Device Code

M = Date Code\* ■ = Pb-Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may
vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

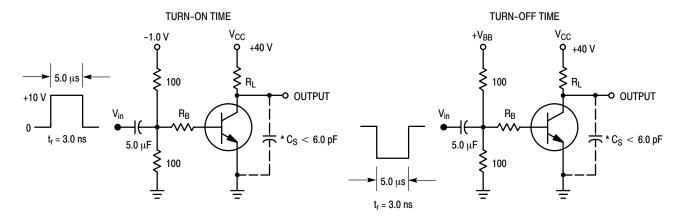
See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS		•		•	•
Collector – Emitter Breakdown Voltage (Note 3) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MMBTA05 MMBTA06, SMMBTA06	V <sub>(BR)CEO</sub>	60 80	- -	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 100 \mu Adc, I_C = 0$ )		V <sub>(BR)EBO</sub>	4.0	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, I <sub>B</sub> = 0)		I <sub>CES</sub>	-	0.1	μAdc
Collector Cutoff Current $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 80 \text{ Vdc}, I_E = 0)$	MMBTA05 MMBTA06, SMMBTA06	I <sub>CBO</sub>	- -	0.1 0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 10 mAdc, $V_{CE}$ = 1.0 Vdc) (I <sub>C</sub> = 100 mAdc, $V_{CE}$ = 1.0 Vdc)		h <sub>FE</sub>	100 100	_ _	-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)		V <sub>CE(sat)</sub>	-	0.25	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 1.0 Vdc)		V <sub>BE(on)</sub>	-	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS		•			
Current – Gain – Bandwidth Product (Note 4) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 2.0 V, f = 100 MHz)		f <sub>T</sub>	100	_	MHz

<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

<sup>4.</sup>  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.



<sup>\*</sup>Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

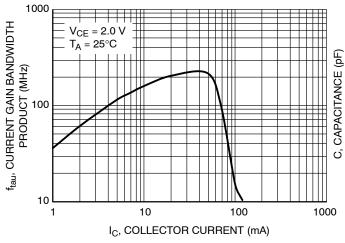


Figure 2. Current Gain Bandwidth Product vs.
Collector Current

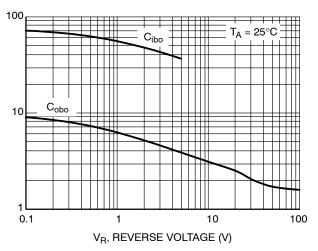


Figure 3. Capacitance

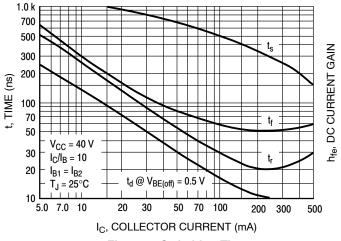


Figure 4. Switching Time

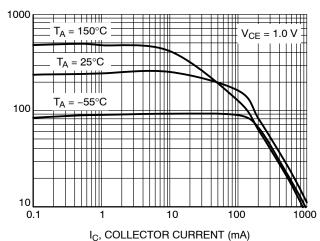


Figure 5. DC Current Gain vs. Collector Current

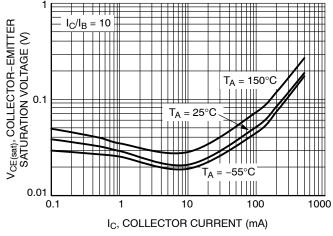


Figure 6. Collector Emitter Saturation Voltage vs. Collector Current

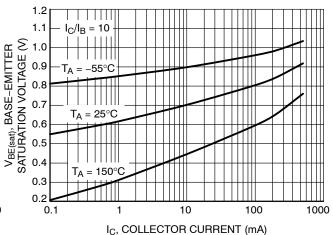


Figure 7. Base Emitter Saturation Voltage vs.
Collector Current

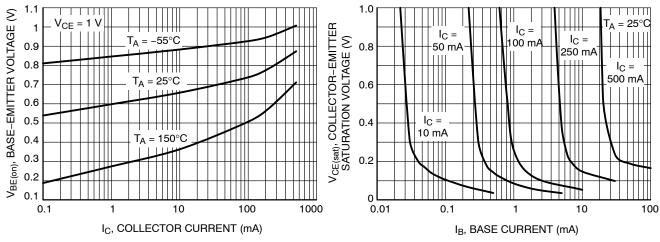


Figure 8. Base Emitter Turn-ON Voltage vs.
Collector Current

Figure 9. Saturation Region

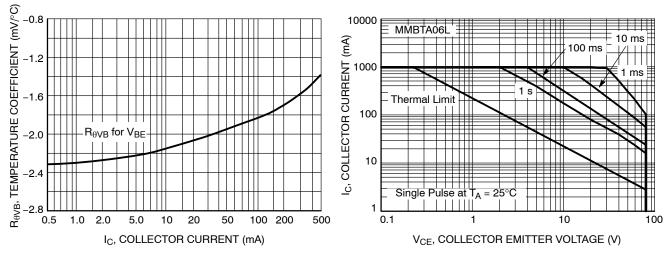


Figure 10. Base-Emitter Temperature Coefficient

Figure 11. Safe Operating Area

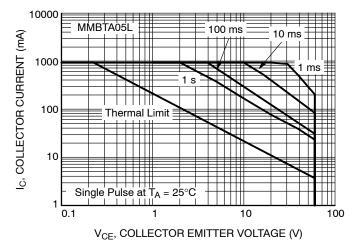


Figure 12. Safe Operating Area

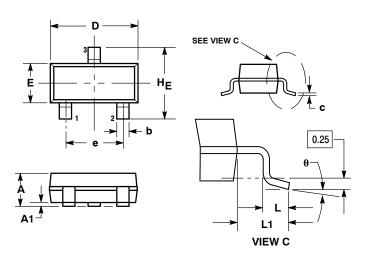
### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBTA05LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBTA05LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBTA06LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SMMBTA06LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBTA06LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBTA06LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### PACKAGE DIMENSIONS

### SOT-23 (TO-236) CASE 318-08 **ISSUE AP**



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: INCH.
   MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
   THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS

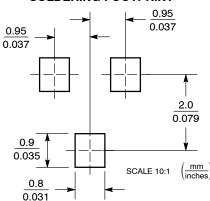
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

STYLE 6:

PIN 1. BASE 2. EMITT

**EMITTER** COLLECTOR

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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